

TSMS-02-1330

March 19, 2004

To: Commissioner for Patents
P.O.Box 1450
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572
28 Davis Avenue
Poughkeepsie, N.Y. 12603

Subject: | Serial No. 10/767,276 01/29/04 |

Kern-Huat Ang et al.

METHOD FOR END POINT DETECTION OF
POLYSILICON CHEMICAL MECHANICAL
POLISHING IN AN ANTI-FUSE MEMORY
DEVICE

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
deposited with the United States Postal Service as first class
mail in an envelope addressed to: Commissioner for Patents,
P.O. Box 1450, Alexandria, VA 22313-1450, on March 25, 2004.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

SpB. Ackerman 3/25/04

U.S. Patent 5,670,410 to Pan, "Method of Forming Integrated CMP Stopper and Analog Capacitor," teaches a method to form an analog capacitor with a topmost electrode comprising polysilicon.

U.S. Patent 6,391,768 to Lee et al., "Process for CMP Removal of Excess Trench or Via Filler Metal which Inhibits Formation of Concave Regions on Oxide Surface of Integrated Circuit Structure," describes a method to chemical mechanical polish a metal layer overlying a dielectric layer.

U.S. Patent 6,261,851 to Li et al., "Optimization of CMP Process by Detecting of Oxide/Nitride Interface Using IR Sytem," describes a method and an apparatus to detect and to monitor ammonia gas given off as a bi-product in a CMP operation.

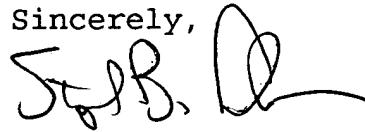
U.S. Patent 6,294,457 to Liu, "Optimized IMD Scheme for Using Organic Low-K Material as IMD Layer," describes a method to prevent particle contamination during an argon (Ar) sputter operation used for pre-cleaning metal.

U.S. Patent 6,008,104 to Schrems, "Method of Fabricating a Trench Capacitor with a Deposited Isolation Collar," discusses a trench capacitor achieved by providing a node dielectric that lines the collar and sidewalls of the bottom of the trench.

U.S. Patent 6,423,628 to Li et al., "Method of Forming Integrated Circuit Structure having Low Dielectric Constant Material and having Silicon Oxynitride Caps Over Closely Spaced Apart Metal Lines," discloses a capping layer of an insulator such as silicon oxynitride formed over horizontally closely spaced apart metal lines on an oxide layer of an integrated circuit structure formed on a semiconductor substrate.

U.S. Patent 6,531,410 to Bertin et al., "Intrinsic Dual Gate Oxide MOSFET Using a Damascene Gate Process," discusses dual gate oxide MOSFET using a damascene gate process.

Sincerely,

A handwritten signature in black ink, appearing to read "Stephen B. Ackerman", with a stylized flourish at the end.

Stephen B. Ackerman,
Reg. No. 37761

INFORMATION DISCLOSURE CITATION
ON AN APPLICATION

MAR 29 2009 (several sheets if necessary)

Document Number (Optional)

TSMC-02-1330

Application Number

10/767,276

Applicant

Kern-Huat Ang et al.

Filing Date

01/29/04

Drawn At Unit

U. S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILED DATE IF APPROPRIATE
	5670410	9/23/97	Pan	437	60	9/25/96
	6391768	5/21/02	Lee et al.	438	633	10/30/00
	6261851	7/17/01	Li et al.	438	8	9/30/99
	6294457	9/25/01	Liu	438	623	2/1/01
	6423628	7/23/02	Li et al.	438	622	10/22/99
	6008104	12/28/99	Schrems	438	386	4/6/98
	6531410	3/11/03	Bertin et al.	438	766	2/27/01

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Portmox Pages, Etc.)

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.